

# CMS13N06H8-HF

**N-Channel**  
**RoHS Device**  
**Halogen Free**



BVDSS	60V
$I_D@V_{GS}=10V, T_C=25^\circ C$	56A
$I_D@V_{GS}=10V, T_A=25^\circ C$	13.8A
$R_{DS(ON)}@V_{GS}=10V, I_D=25A$	5.1mΩ(typ)
$R_{DS(ON)}@V_{GS}=4.5V, I_D=25A$	7.4mΩ(typ)

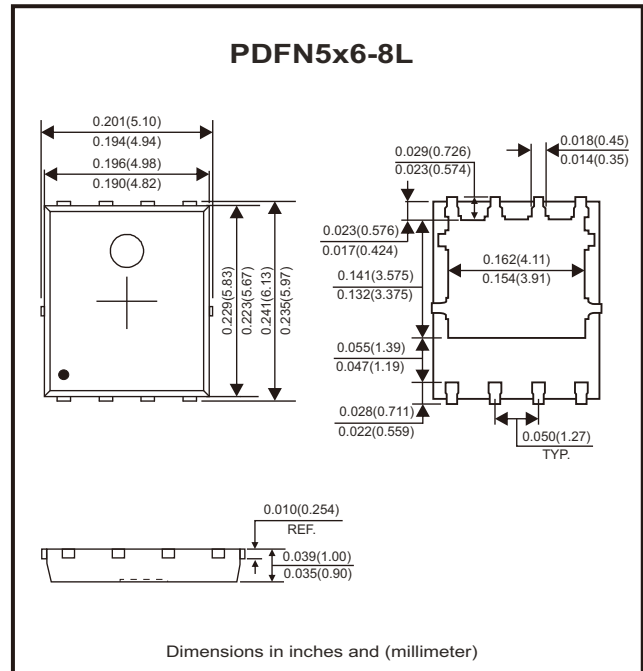
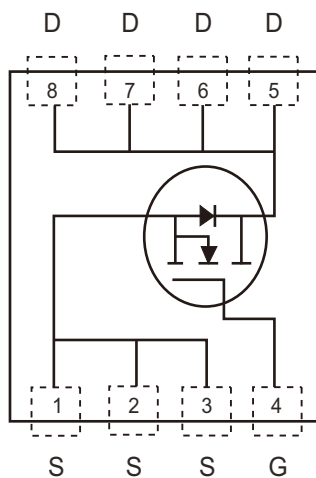
## Features

- Single drive requirement.
- Low On-resistance.
- Fast switching characteristic.
- Repetitive avalanche rated.

## Mechanical data

- Case : PDFN5x6-8L, molded plastic.
- Epoxy : UL 94V-0 rated flame retardant.
- Lead: Pure tin plated.

## Circuit Diagram



**Absolute Maximum Ratings** (at  $T_a=25^\circ\text{C}$  unless otherwise noted)

Parameter		Symbol	10s	Steady State	Unit
Drain-source voltage		$V_{DS}$	60		V
Gate-source voltage		$V_{GS}$	$\pm 20$		V
Drain current-continuous @ $T_c=25^\circ\text{C}, V_{GS}=10\text{V}$ (silicon limit) (Note 1)		$I_D$	80		A
Continuous drain current @ $T_c=25^\circ\text{C}, V_{GS}=10\text{V}$ (package limit) (Note 1)			56		A
Continuous drain current @ $T_c=100^\circ\text{C}, V_{GS}=10\text{V}$ (Note 1)			35		A
Continuous drain current @ $T_A=25^\circ\text{C}, V_{GS}=10\text{V}$ (Note 2)		$I_{DSM}$	20.8	13.8	A
Continuous drain current @ $T_A=70^\circ\text{C}, V_{GS}=10\text{V}$ (Note 2)			16.6	11.0	A
Continuous drain current @ $T_A=85^\circ\text{C}, V_{GS}=10\text{V}$ (Note 2)			15.0	9.9	A
Pulsed drain current (Note 3)		$I_{DM}$	224 * 1		A
Avalanche current (Note 3)		$I_{AS}$	40		A
Avalanche energy @ $L=0.1\text{mH}, I_D=40\text{A}, V_{DD}=30\text{V}$ (Note 2,4)		$E_{AS}$	80		mJ
Repetitive avalanche energy @ $L=0.05\text{mH}$ (Note 3)		$E_{AR}$	10 * 2		
Total power dissipation	$T_c=25^\circ\text{C}$ (Note 1)	$P_D$	83		W
	$T_c=100^\circ\text{C}$ (Note 1)		33		
	$T_A=25^\circ\text{C}$ (Note 2)	$P_{DSM}$	5.7	2.5	
	$T_A=70^\circ\text{C}$ (Note 2)		4.0	1.8	
	$T_A=85^\circ\text{C}$ (Note 2)		3.6	1.6	
Operating temperature range		$T_J$	-55~+150		$^\circ\text{C}$
Storage temperature range		$T_{STG}$	-55 to +150		$^\circ\text{C}$

**Thermal Data**

Parameter		Symbol	Typical	Maximum	Unit
Thermal resistance, junction to ambient (Note 2)	$t \leq 10\text{s}$	$R_{\theta JA}$	18	22	$^\circ\text{C/W}$
	Steady state		42	50	$^\circ\text{C/W}$
Thermal resistance	junction to case	$R_{\theta JC}$	1.4	1.5	$^\circ\text{C/W}$

Notes: 1. The power dissipation  $P_D$  is based on  $T_{J(\text{MAX})}=150^\circ\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

2. The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2 oz. copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The power dissipation  $P_{DSM}$  is based on  $R_{\theta JA}$  and the maximum allowed junction temperature of  $150^\circ\text{C}$ . The value in any given application depends on the user's specific board design.

3. Repetitive rating, pulse width limited by junction temperature  $T_{J(\text{MAX})}=150^\circ\text{C}$ . Ratings are based on low frequency and low duty cycles to keep initial  $T_J=25^\circ\text{C}$ .

4. 100% tested by conditions of  $L=0.1\text{mH}, I_{AS}=10\text{A}, V_{GS}=10\text{V}, V_{DD}=30\text{V}$ .

**Electrical Characteristics** (  $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
<b>Static</b>						
Drain-source breakdown voltage	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	$BV_{DSS}$	60			V
Gate-threshold voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	$V_{GS(th)}$	1.4		2.6	V
Forward transconductance (Note 1)	$V_{DS} = 10\text{V}, I_D = 30\text{A}$	$G_{FS}$		30		S
Gate-Source leakage current	$V_{GS} = \pm 20\text{V}$	$I_{GSS}$			$\pm 100$	nA
Zero gate voltage drain current	$V_{DS} = 48\text{V}, V_{GS} = 0\text{V}$	$I_{DSS}$			1	$\mu\text{A}$
	$V_{DS} = 48\text{V}, V_{GS} = 0\text{V}, T_J = 125^{\circ}\text{C}$	$I_{DSS}$			25	
Static drain-source on-resistance (Note 1)	$V_{GS} = 10\text{V}, I_D = 25\text{A}$	$R_{DS(on)}$		5.1	6.4	m $\Omega$
	$V_{GS} = 4.5\text{V}, I_D = 25\text{A}$			7.4	9.6	
<b>Dynamic</b>						
Input capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	$C_{iss}$		1619		pF
Output capacitance		$C_{oss}$		275		
Reverse transfer capacitance		$C_{rss}$		143		
Total gate charge (Note 1,2)	$V_{DS} = 48\text{V}, V_{GS} = 10\text{V}, I_D = 25\text{A}$	$Q_g$		42.8		nC
Gate-source charge (Note 1,2)		$Q_{gs}$		5.8		
Gate-drain charge (Note 1,2)		$Q_{gd}$		15.6		
Turn-on delay time (Note 1,2)	$V_{DS} = 30\text{V}, I_D = 1\text{A},$ $V_{GS} = 10\text{V}, R_{GS} = 6\Omega$	$t_{d(on)}$		15.2		ns
Turn-on rise time (Note 1,2)		$t_r$		22.4		
Turn-off delay time (Note 1,2)		$t_{d(off)}$		74		
Turn-off fall time (Note 1,2)		$t_f$		36		
Gate resistance	$f = 1\text{MHz}$	$R_g$		4		
<b>Source-Drain Diode</b>						
Drain-source diode forward current (Note 1)		$I_S$			56	A
Pulse diode forward current (Note 3)		$I_{SM}$			224	
Drain-source diode forward voltage (Note 1)	$V_{GS} = 0\text{V}, I_S = 25\text{A}$	$V_{SD}$		0.82	1.2	V
Body Diode Reverse Recovery Time	$I_F = 25\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$	$t_{rr}$		18		nS
Body Diode Reverse Recovery Charge		$Q_{rr}$			12	

- Notes: 1. Pulse test : Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$ .  
2. Independent of operating temperature.  
3. Pulse width limited by maximum junction temperature.

## Rating and Characteristic Curves (CMS13N06H8-HF)

Fig.1 - Typical Output Characteristics

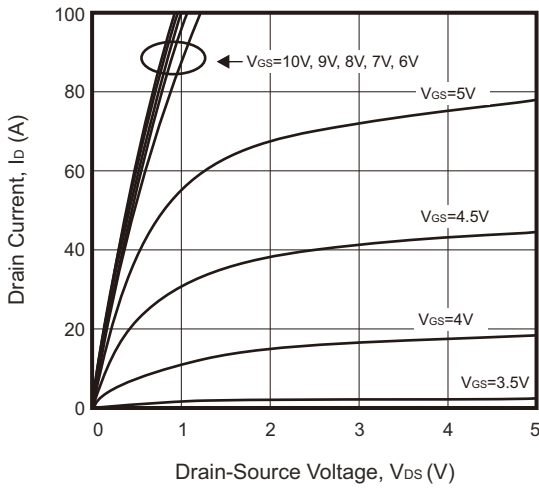


Fig.2 - Static Drain-Source On-State Resistance VS Drain Current

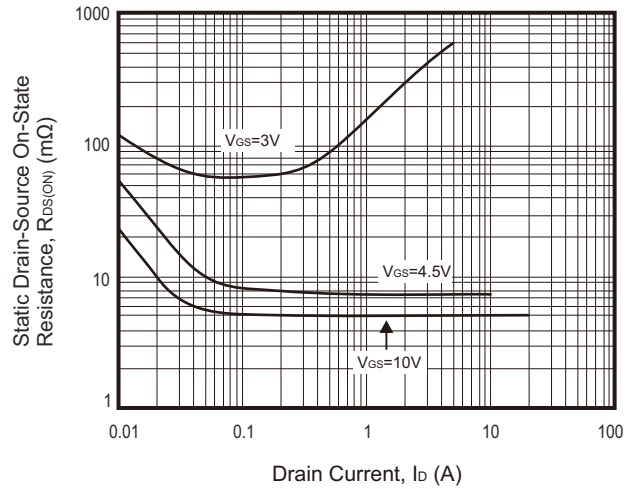


Fig.3 - Static Drain-Source On-State Resistance VS Gate-Source Voltage

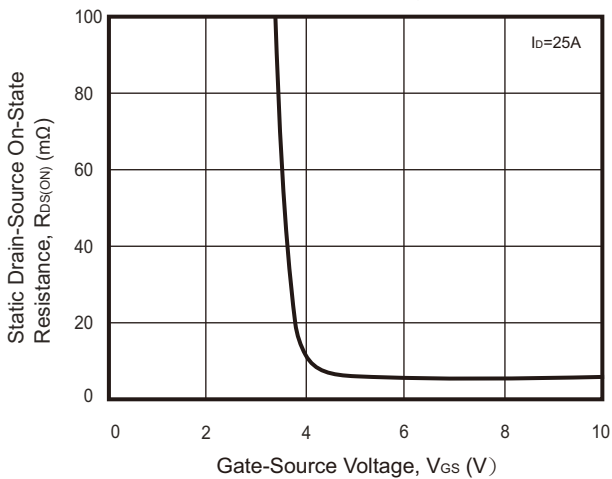


Fig.4 - Capacitance VS Drain-Source Voltage

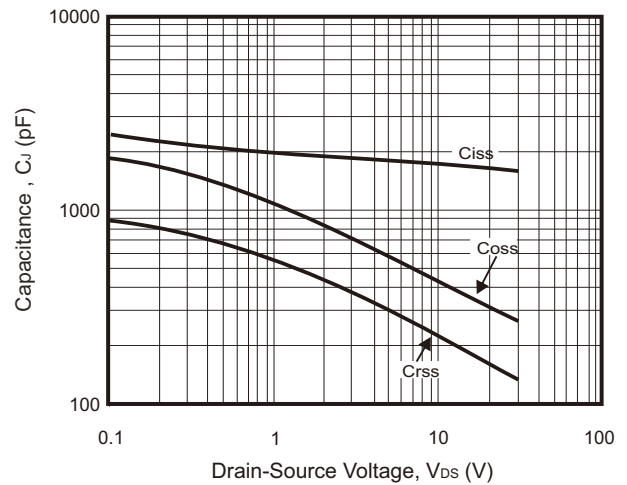


Fig.5 - Forward Transfer Admittance VS Drain Current

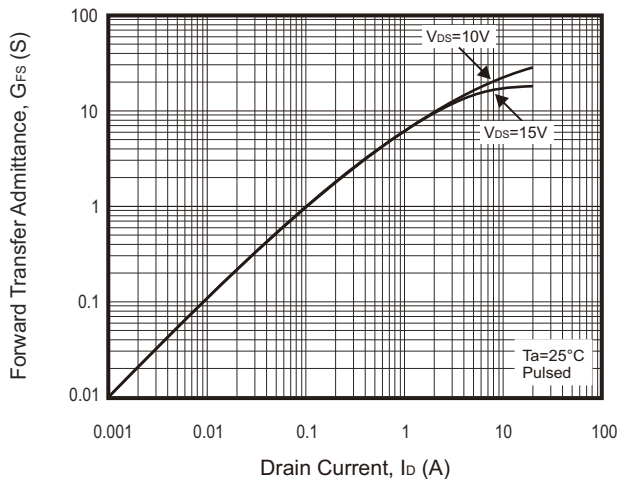
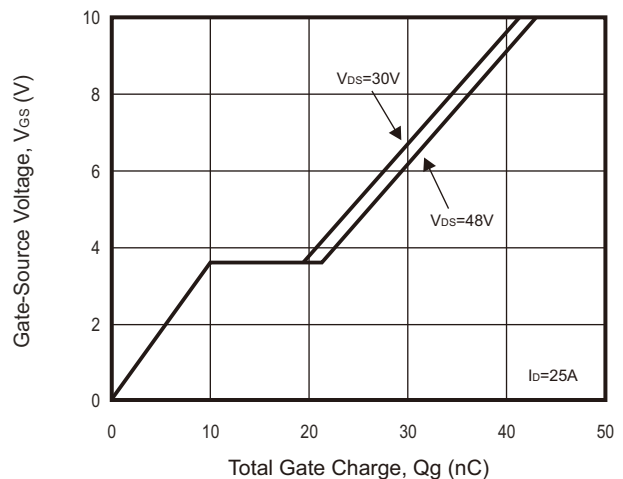
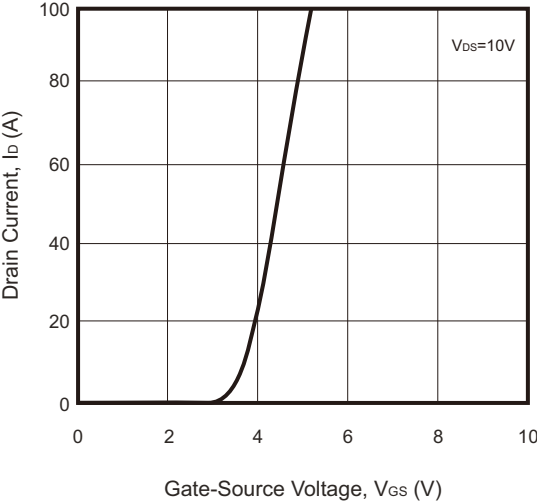


Fig.6 - Gate Charge Characteristics

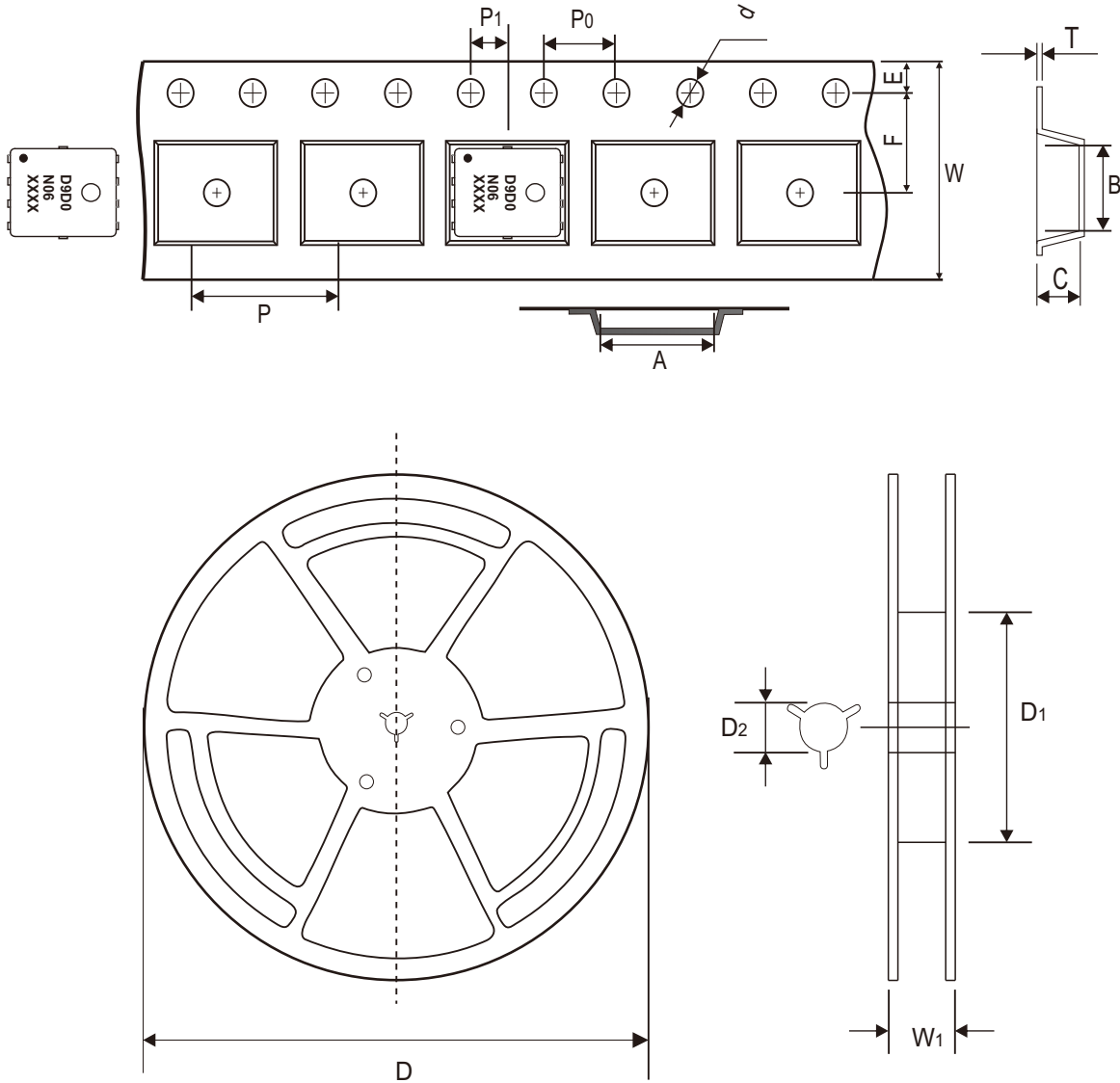


Rating and Characteristic Curves (CMS13N06H8-HF)

Fig.7 - Typical Transfer Characteristics



Reel Taping Specification

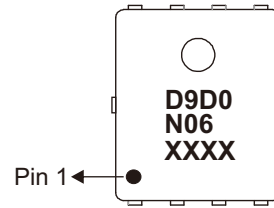


PDFN5x6 8L	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	6.30 ± 0.10	5.30 ± 0.10	1.10 ± 0.10	1.50 + 0.10 - 0.00	330.00 ± 1.00	100.00 ± 0.50	13.00 ± 0.20
	(inch)	0.248 ± 0.004	0.209 ± 0.004	0.043 ± 0.004	0.059 + 0.004 - 0.000	12.992 ± 0.039	3.937 ± 0.020	0.512 ± 0.008

PDFN5x6 8L	SYMBOL	E	F	P	P0	P1	T	W	W1
	(mm)	1.75 ± 0.10	5.50 ± 0.05	8.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.05	0.25 ± 0.02	12.00 + 0.30 - 0.10	17.60 + 1.00 - 0.00
	(inch)	0.069 ± 0.004	0.217 ± 0.002	0.315 ± 0.004	0.157 ± 0.004	0.079 ± 0.002	0.010 ± 0.001	0.472 + 0.012 - 0.004	0.693 + 0.039 - 0.000

## Marking Code

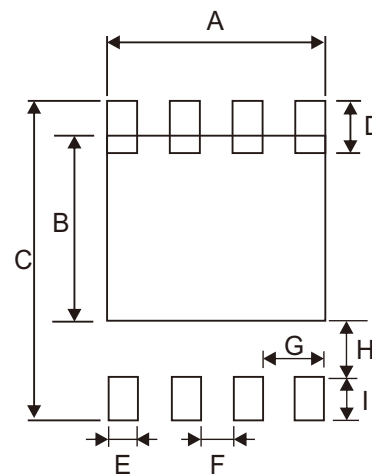
Part Number	Marking Code
CMS13N06H8-HF	D9D0N06 XXXX



XXXX = Control code

## Suggested P.C.B. PAD Layout

SIZE	PDFN5x6-8L	
	(mm)	(inch)
A	4.42	0.174
B	3.81	0.150
C	6.61	0.260
D	1.02	0.040
E	0.61	0.024
F	0.66	0.026
G	1.27	0.050
H	1.23	0.048
I	0.86	0.034



## Standard Packaging

Case Type	REEL PACK	
	REEL ( pcs )	Reel Size (inch)
PDFN5x6-8L	3,000	13